MC14572UB

Hex Gate

The MC14572UB hex functional gate is constructed with MOS P–channel and N–channel enhancement mode devices in a single monolithic structure. These complementary MOS logic gates find primary use where low power dissipation and/or high noise immunity is desired. The chip contains four inverters, one NOR gate and one NAND gate.

- Diode Protection on All Inputs
- Single Supply Operation
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- NOR Input Pin Adjacent to V_{SS} Pin to Simplify Use As An Inverter
- NAND Input Pin Adjacent to V_{DD} Pin to Simplify Use As An Inverter
- NOR Output Pin Adjacent to Inverter Input Pin For OR Application
- NAND Output Pin Adjacent to Inverter Input Pin For AND Application
- Capable of Driving Two Low–power TTL Loads or One Low–Power Schottky TTL Load over the Rated Temperature Range

MAXIMUM RATINGS (Voltages Referenced to V_{SS}) (Note 2.)

Symbol	Parameter	Value	Unit
V_{DD}	DC Supply Voltage Range	–0.5 to +18.0	V
V_{in}, V_{out}	Input or Output Voltage Range (DC or Transient)	–0.5 to V_{DD} + 0.5	V
I_{in}, I_{out}	Input or Output Current (DC or Transient) per Pin	±10	mA
P_D	Power Dissipation, per Package (Note 3.)	500	mW
T_A	Ambient Temperature Range	–55 to +125	°C
T_{stg}	Storage Temperature Range	–65 to +150	°C
T_L	Lead Temperature (8–Second Soldering)	260	°C

2. Maximum Ratings are those values beyond which damage to the device may occur.
3. Temperature Derating:
   Plastic “P and D/DW” Packages: – 7.0 mW/°C From 65°C To 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $V_{SS} \leq (V_{in} \text{ or } V_{out}) \leq V_{DD}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.

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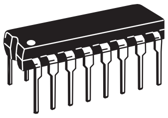
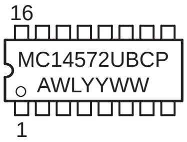
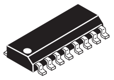
MARKING DIAGRAMS

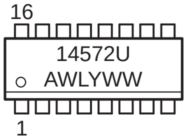


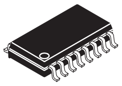
PDIP–16
P SUFFIX
CASE 648



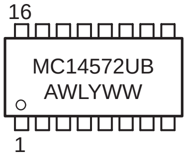


SOIC–16
D SUFFIX
CASE 751B





SOEIAJ–16
F SUFFIX
CASE 966



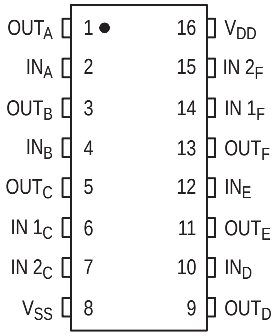
A	= Assembly Location
WL or L	= Wafer Lot
YY or Y	= Year
WW or W	= Work Week

ORDERING INFORMATION

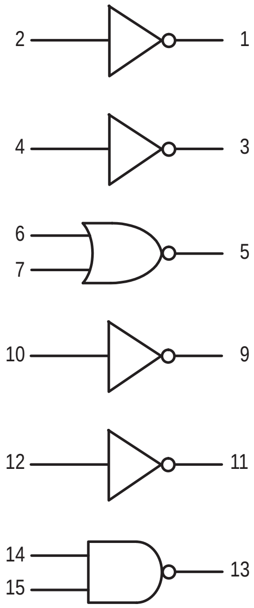
Device	Package	Shipping
MC14572UBCP	PDIP–16	2000/Box
MC14572UBD	SOIC–16	48/Rail
MC14572UBDR2	SOIC–16	2500/Tape & Reel
MC14572UBF	SOEIAJ–16	See Note 1.
MC14572UBFEL	SOEIAJ–16	See Note 1.

1. For ordering information on the EIAJ version of the SOIC packages, please contact your local ON Semiconductor representative.

PIN ASSIGNMENT

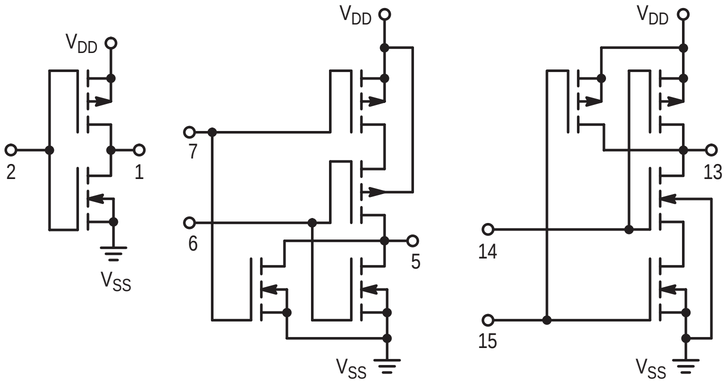


LOGIC DIAGRAM



V_{DD} = PIN 16
V_{SS} = PIN 8

CIRCUIT SCHEMATIC



ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

Characteristic	Symbol	V_{DD}	– 55°C		25°C			125°C		Unit
		Vdc	Min	Max	Min	Typ [4.]	Max	Min	Max	
Output Voltage "0" Level	V_{OL}	5.0	—	0.05	—	0	0.05	—	0.05	Vdc
V_{in} = V_{DD} or 0		10	—	0.05	—	0	0.05	—	0.05	
		15	—	0.05	—	0	0.05	—	0.05	
V_{in} = 0 or V_{DD} "1" Level	V_{OH}	5.0	4.95	—	4.95	5.0	—	4.95	—	Vdc
		10	9.95	—	9.95	10	—	9.95	—	
		15	14.95	—	14.95	15	—	14.95	—	
Input Voltage "0" Level	V_{IL}									Vdc
(V_O = 4.5 or 0.5 Vdc)		5.0	—	1.0	—	2.25	1.0	—	1.0	
(V_O = 9.0 or 1.0 Vdc)		10	—	2.0	—	4.50	2.0	—	2.0	
(V_O = 13.5 or 1.5 Vdc)		15	—	2.5	—	6.75	2.5	—	2.5	
"1" Level	V_{IH}									Vdc
(V_O = 0.5 or 4.5 Vdc)		5.0	4.0	—	4.0	2.75	—	4.0	—	
(V_O = 1.0 or 9.0 Vdc)		10	8.0	—	8.0	5.50	—	8.0	—	
(V_O = 1.5 or 13.5 Vdc)		15	12.5	—	12.5	8.25	—	12.5	—	
Output Drive Current	I_{OH}									mAdc
(V_{OH} = 2.5 Vdc) Source		5.0	– 1.2	—	– 1.0	– 1.7	—	– 0.7	—	
(V_{OH} = 4.6 Vdc)		5.0	– 0.25	—	– 0.2	– 0.36	—	– 0.14	—	
(V_{OH} = 9.5 Vdc)		10	– 0.62	—	– 0.5	– 0.9	—	– 0.35	—	
(V_{OH} = 13.5 Vdc)		15	– 1.8	—	– 1.5	– 3.5	—	– 1.1	—	
(V_{OL} = 0.4 Vdc) Sink	I_{OL}	5.0	0.64	—	0.51	0.88	—	0.36	—	mAdc
(V_{OL} = 0.5 Vdc)		10	1.6	—	1.3	2.25	—	0.9	—	
(V_{OL} = 1.5 Vdc)		15	4.2	—	3.4	8.8	—	2.4	—	
Input Current	I_{in}	15	—	±0.1	—	±0.00001	±0.1	—	±1.0	µAdc
Input Capacitance (V_{in} = 0)	C_{in}	—	—	—	—	5.0	7.5	—	—	pF
Quiescent Current (Per Package)	I_{DD}	5.0	—	0.25	—	0.0005	0.25	—	7.5	µAdc
		10	—	0.5	—	0.0010	0.5	—	15	
		15	—	1.0	—	0.0015	1.0	—	30	
Total Supply Current [5.] [6.] (Dynamic plus Quiescent, Per Package) (C_L = 50 pF on all outputs, all buffers switching)	I_T	5.0	I_T = (1.89 µA/kHz) f + I_{DD}							µAdc
		10	I_T = (3.80 µA/kHz) f + I_{DD}							
		15	I_T = (5.68 µA/kHz) f + I_{DD}							

4. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.
5. The formulas given are for the typical characteristics only at 25°C.
6. To calculate total supply current at loads other than 50 pF:

$$I_T(C_L) = I_T(50\text{ pF}) + (C_L - 50)\,Vfk$$

where: I_T is in µA (per package), C_L in pF, V = (V_{DD} – V_{SS}) in volts, f in kHz is input frequency, and k = 0.006.

SWITCHING CHARACTERISTICS [7.] (C_L = 50 pF, T_A = 25°C)

Characteristic	Symbol	V_{DD}	Min	Typ [8.]	Max	Unit
Output Rise Time	t_{TLH}					ns
t_{TLH} = (3.0 ns/pF) C_L + 30 ns		5.0	—	180	360	
t_{TLH} = (1.5 ns/pF) C_L + 15 ns		10	—	90	180	
t_{TLH} = (1.1 ns/pF) C_L + 10 ns		15	—	65	130	
Output Fall Time	t_{THL}					ns
t_{THL} = (1.5 ns/pF) C_L + 25 ns		5.0	—	100	200	
t_{THL} = (0.75 ns/pF) C_L + 12.5 ns		10	—	50	100	
t_{THL} = (0.55 ns/pF) C_L + 9.5 ns		15	—	40	80	
Propagation Delay Time	t_{PLH}, t_{PHL}					ns
t_{PLH}, t_{PHL} = (1.7 ns/pF) C_L + 5 ns		5.0	—	90	180	
t_{PLH}, t_{PHL} = (0.66 ns/pF) C_L + 17 ns		10	—	50	100	
t_{PLH}, t_{PHL} = (0.5 ns/pF) C_L + 15 ns		15	—	40	80	

7. The formulas given are for the typical characteristics only at 25°C.
8. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

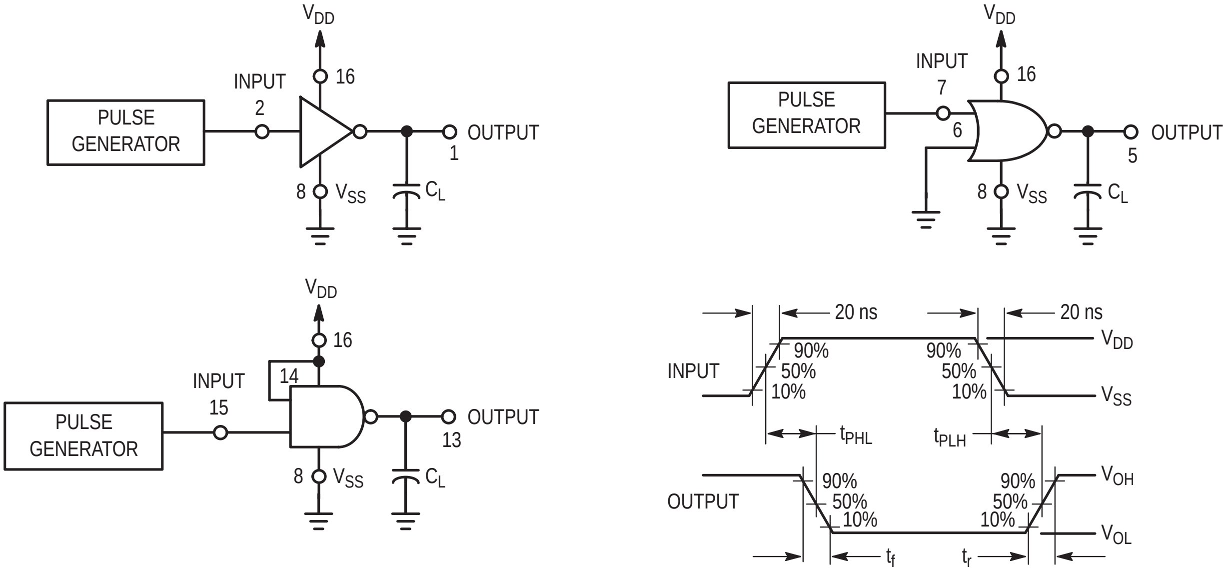
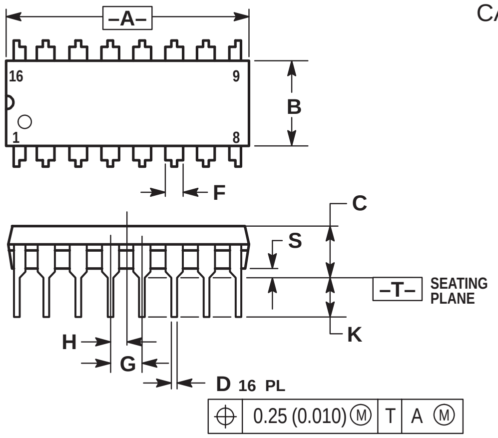
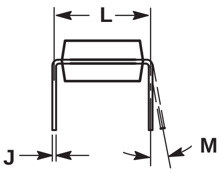


Figure 1. Switching Time Test Circuits and Waveforms

PACKAGE DIMENSIONS

PDIP–16
P SUFFIX
PLASTIC DIP PACKAGE
CASE 648–08
ISSUE R





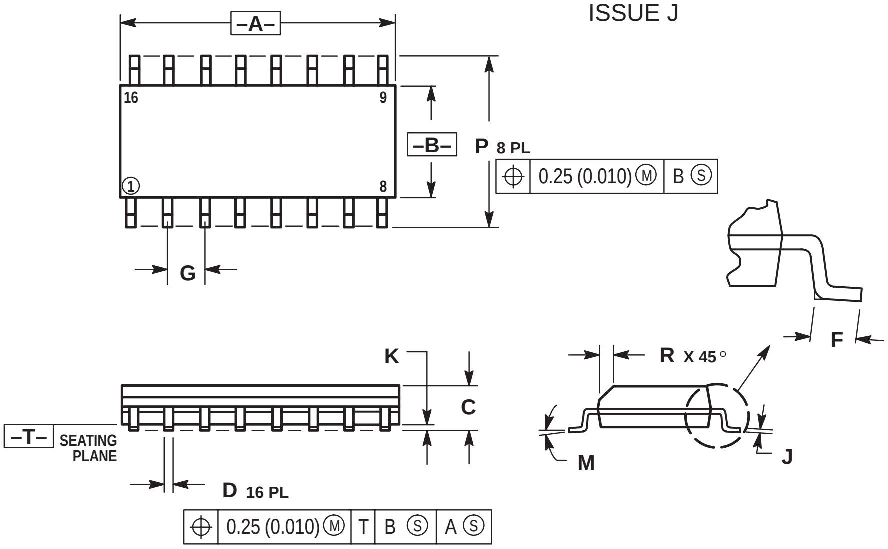
NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
5. ROUNDED CORNERS OPTIONAL.

	INCHES		MILLIMETERS	
DIM	**MIN**	**MAX**	**MIN**	**MAX**
A	0.740	0.770	18.80	19.55
B	0.250	0.270	6.35	6.85
C	0.145	0.175	3.69	4.44
D	0.015	0.021	0.39	0.53
F	0.040	0.70	1.02	1.77
G	0.100 BSC		2.54 BSC	
H	0.050 BSC		1.27 BSC	
J	0.008	0.015	0.21	0.38
K	0.110	0.130	2.80	3.30
L	0.295	0.305	7.50	7.74
M	0°	10°	0°	10°
S	0.020	0.040	0.51	1.01

PACKAGE DIMENSIONS

SOIC–16
D SUFFIX

PLASTIC SOIC PACKAGE
CASE 751B–05
ISSUE J



NOTES:

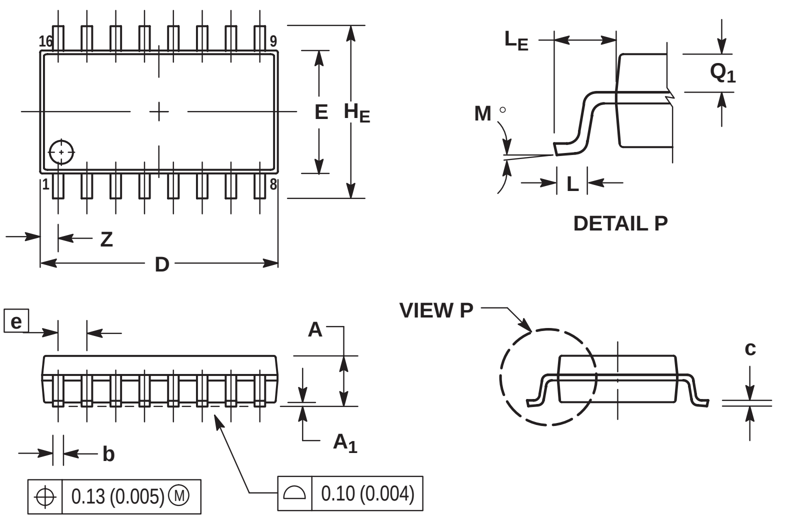
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	9.80	10.00	0.386	0.393
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

PACKAGE DIMENSIONS

SOEIAJ–16
F SUFFIX

PLASTIC EIAJ SOIC PACKAGE
CASE 966–01
ISSUE O



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	—	2.05	—	0.081
A_1	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
c	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
e	1.27 BSC		0.050 BSC	
H_E	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
L_E	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10 °
Q_1	0.70	0.90	0.028	0.035
Z	—	0.78	—	0.031

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